

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1KV (HBM)
- **Lead Free/RoHS Compliant (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.002 grams (approximate)



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage (Note 1)	V _{GS}	±20	V
Drain Current (Note 1)	I _D	115 73 800	mA
		Continuous	
		Continuous @ 100°C	
		Pulsed	

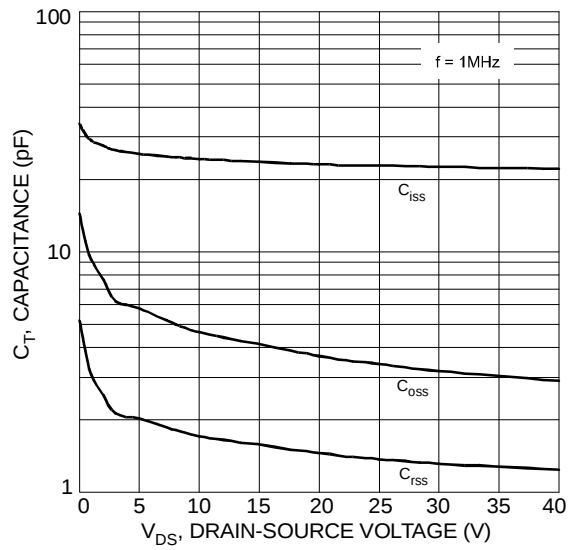
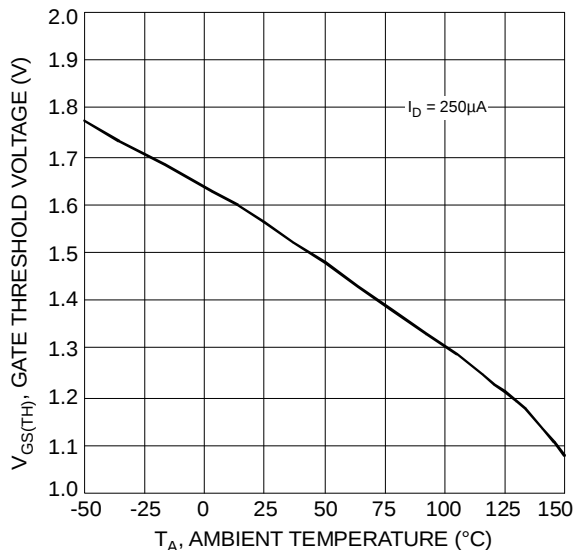
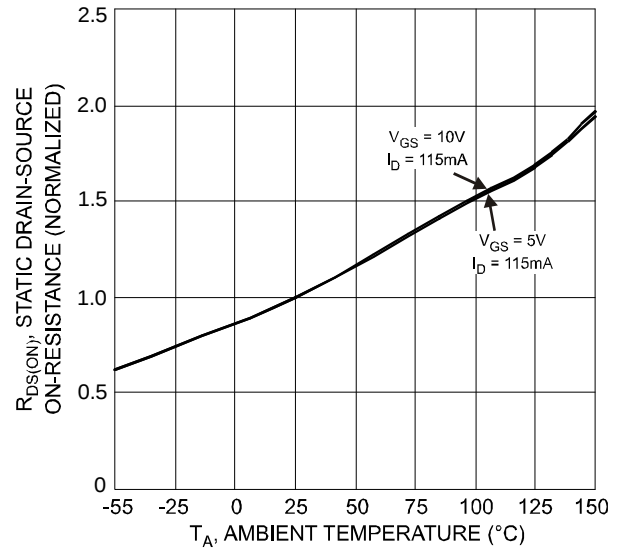
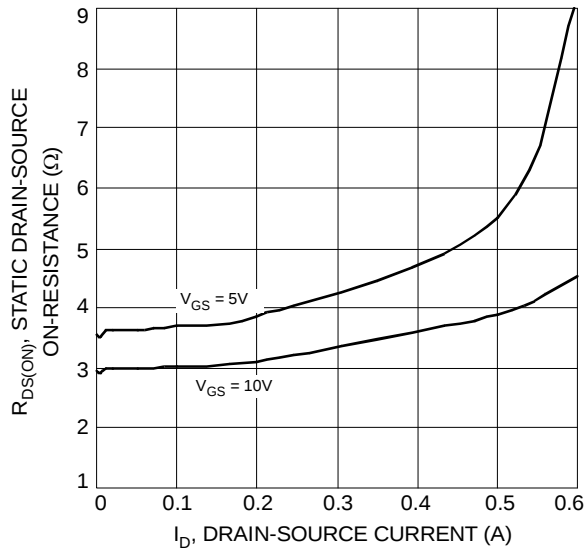
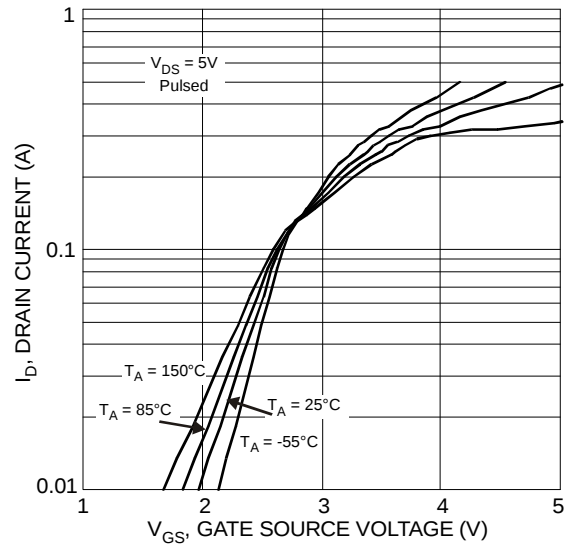
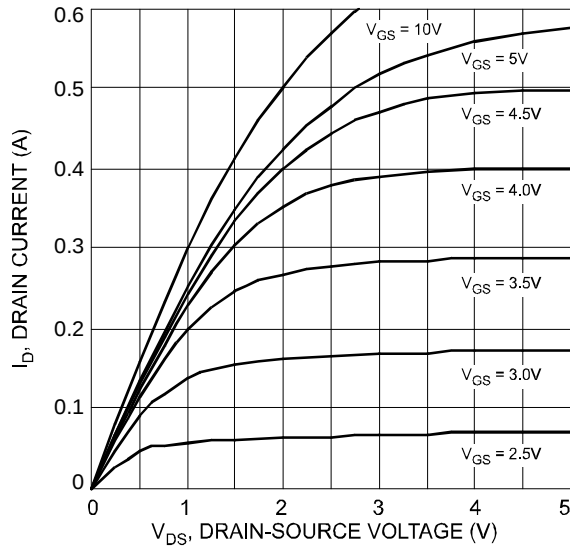
Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation	P _D	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	70	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0 500	μA	@ T _C = 25°C @ T _C = 125°C V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±5	μA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	1.2	—	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS (ON)}	—	3.5 3.0	6 5	Ω	@ T _J = 25°C @ T _J = 125°C V _{GS} = 5.0V, I _D = 0.115A V _{GS} = 10V, I _D = 0.115A
Forward Transconductance	g _{FS}	80	—	—	mS	V _{DS} = 10V, I _D = 0.115A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iSS}	—	23	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oSS}	—	3.4	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	1.4	—	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = 30V, I _D = 0.115A, R _L = 150Ω, V _{GEN} = 10V, R _{GEN} = 25Ω
Turn-Off Delay Time	t _{D(OFF)}	—	33	—	ns	

- Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. No purposefully added lead.
 3. Short duration pulse test used to minimize self-heating effect.



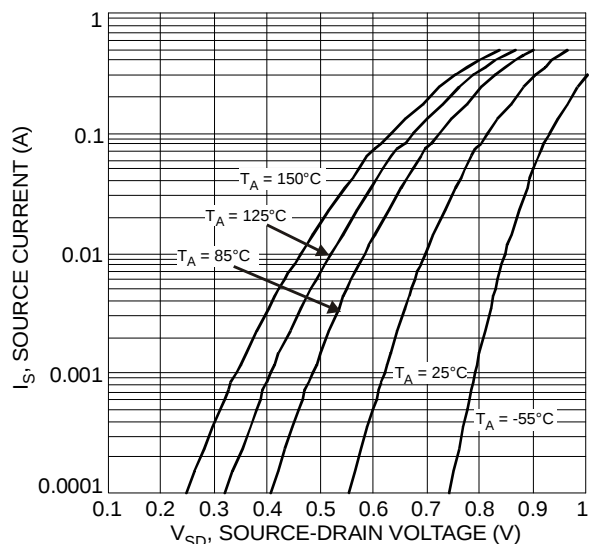


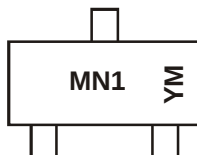
Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN66D0LT-7	SOT-523	3000/Tape & Reel

 Notes: 4. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



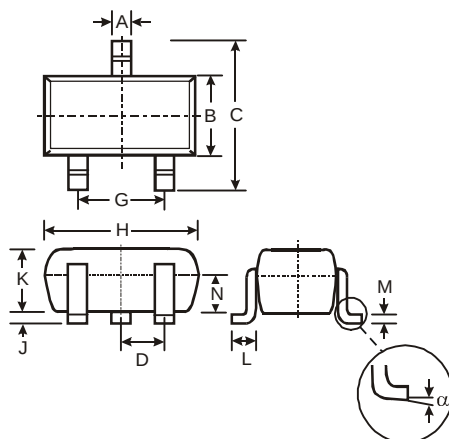
MN1 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: V = 2008
 M = Month ex: 9 = September

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

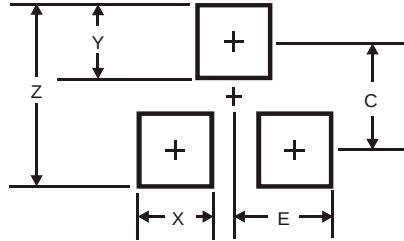
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-523			
Dim	Min	Max	Typ
A	0.15	0.30	0.22
B	0.75	0.85	0.80
C	1.45	1.75	1.60
D	—	—	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
J	0.00	0.10	0.05
K	0.60	0.80	0.75
L	0.10	0.30	0.22
M	0.10	0.20	0.12
N	0.45	0.65	0.50
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.8
X	0.4
Y	0.51
C	1.3
E	0.7

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